multicomp PRO

General Purpose Amplifier / Switches





Compliant

RoHS

Pin Configuration

1. Emitter 2. Base 3. Collector

Feature

NPN Silicon Planar Epitaxial Transistors

Absolute Maximum Ratings

Description	Symbol	Values	Unit		
Collector-Emitter Voltage	VCEO	25			
Collector-Base Voltage	Vсво	30	V		
Emitter-Base Voltage	Vebo	5			
Collector Current Continuous	lc	0.2	A		
Power Dissipation at T _A = 25°C Derate Above 25°C	D -	0.6 2.28	W		
Power Dissipation at Tc = 25°C Derate Above 25°C	PD	1 6.67	mW / °C		
Operating and Storage Junction Temperature Range	TJ, Tsтg	-65 to +200	°C		
Thermal Resistance					
Junction to Case	Rth (j-c)	175	°C / W		

Electrical Characteristics (T_A = 25°C unless otherwise specified)

Description	Symbol	Test Condition	Minimum	Maximum	Unit
Collector-Emitter Voltage	VCEO	Ic = 2 mA, Iв = 0	25	-	V
Collector-Base Voltage	Vebo	Iε = 10μΑ, Ic = 0	5	-	v
Collector-Cut off Current	Ісво	V _{CB} = 25V, I _E = 0 Tamb = 125°С V _{CB} = 25 V, I _E = 0	-	15 4	nA μA
DC Current	hfe	Ic = 10μΑ, Vcε = 5 V B Group C Group	40 100		
		Ic = 2mA, Vc _E = 5V B Group C Group	200 200 420	800 450 800	-
Base Emitter Saturation Voltage	VBE (sat)	Ic = 10mA, Iв = 0.5mA	-	0.83 1.05	v
Collector Emitter Saturation Voltage	VCE (sat)	Ic = 100mA, Iв = 5mA	-	0.25 0.6	

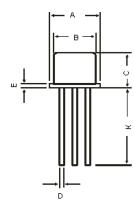
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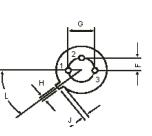


Low Power Bipolar Transistors BC109 Series

Description	Symbol	Test Condition	Minimum	Maximum	Unit
Base Emitter on Voltage	VBE (on)	Ic = 2 mA, Vce = 5V Ic = 10 mA, Vce = 5V	0.55 -	0.7 0.77	V
Collector Knee Voltage	Vce (K)	Ic = 10mA, I _B = The Value for Which Ic = 11mA at V _{CE} = 1V	-	0.6	V
Transition Frequency	ft	Vce = 5V, Ic = 10mA f = 100MHz	150	-	MHz
Noise Figure	nF	$V_{CE} = 5V$, Ic = 0.2mA Rg = 2k Ω F = 30Hz to 15kHz F = 1kHz, B = 200Hz	-	4	dB
Output Capacitance	Cobo	Vсв = 10V, f = 1MHz	-	4.5	pF
Small Signal Current Gain	h _{fe}	All f = 1kHz Ic = 2mA, Vcɛ = 5V B Group C Group	240 240 450	900 500 900	-
Input Impedance	h _{ie}	Ic = 2mA, VcE = 5V B Group C Group	3.2 6	8.5 15	kΩ
Output Admittance	hoe	Ic = 2mA, VcE = 5V B Group C Group	-	60 110	μΩ

TO-18 Metal Can Package





Dim.	Min.	Max.
А	5.24	5.84
В	4.52	4.97
С	4.31	5.33
D	0.4	0.53
Е	-	0.76

Dim.	Min.	Max.
F	-	1.27
G	-	2.97
Н	0.91	1.17
J	0.71	1.21
К	12.7	-
L	45°	

Part Number Table

Description	Part Number	
Low Power Bipolar Transistor, NPN, 25V, 150MHz, 600mW	BC109	
	BC109B	
	BC109C	

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